

**BRCS2321MA**  
Rev.A Sep.-2022

SOT-23            P  
G- CHANNEL MOSFET in a SOT-23 Plastic Package.

Ultra Low on-resistance. fast switching.Low on voltage, HF Product.

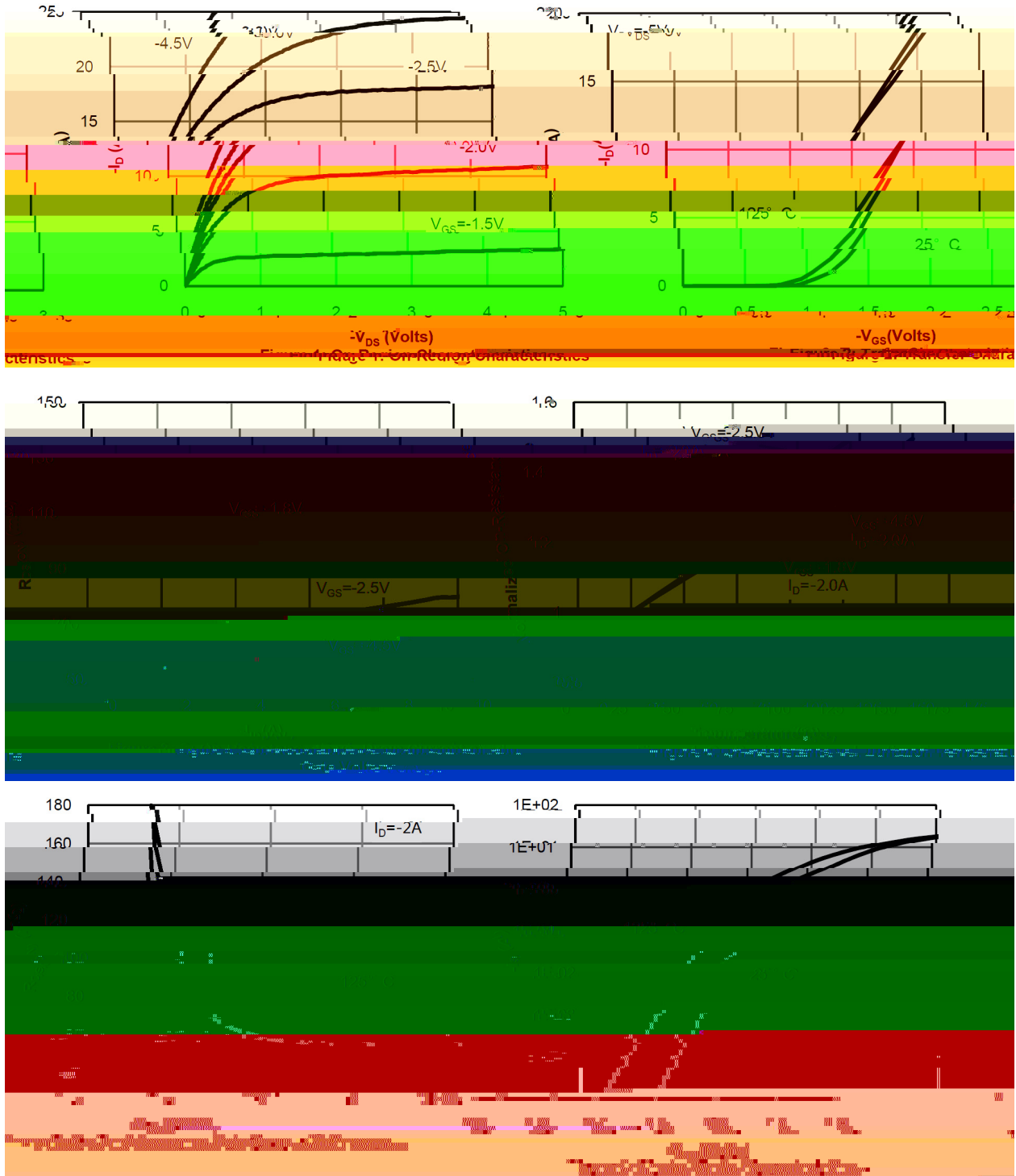
**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit	
Drain–Source Voltage	V <sub>DSS</sub>	-20	V	
Gate–Body Leakage Voltage	V <sub>GSS</sub>	±12	V	
Drain Current – Continuous	I <sub>D</sub>	-3	A	
Pulsed Drain Current	I <sub>DM</sub>	-15	A	
Power Dissipation	P <sub>D</sub>	1.4	W	
Operating and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 150		
Maximum Junction-to-Ambient	t 10s	R <sub>JA</sub>	90	/W
Maximum Junction-to-Ambient	Steady-State		125	/W
Maximum Junction-to-Lead	Steady-State	R <sub>JL</sub>	80	/W

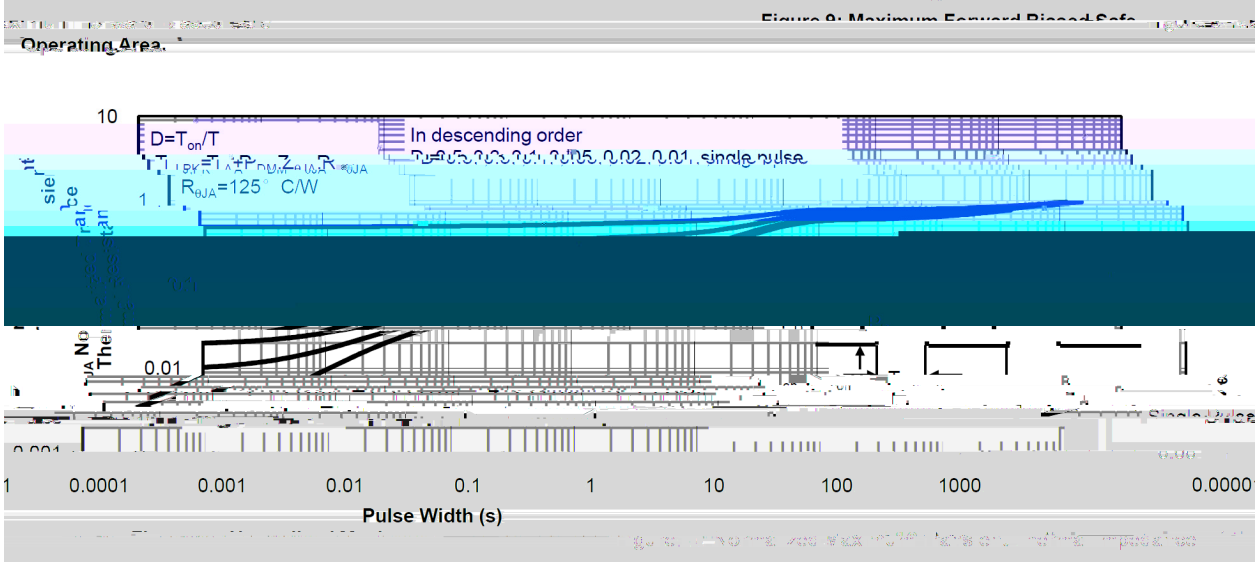
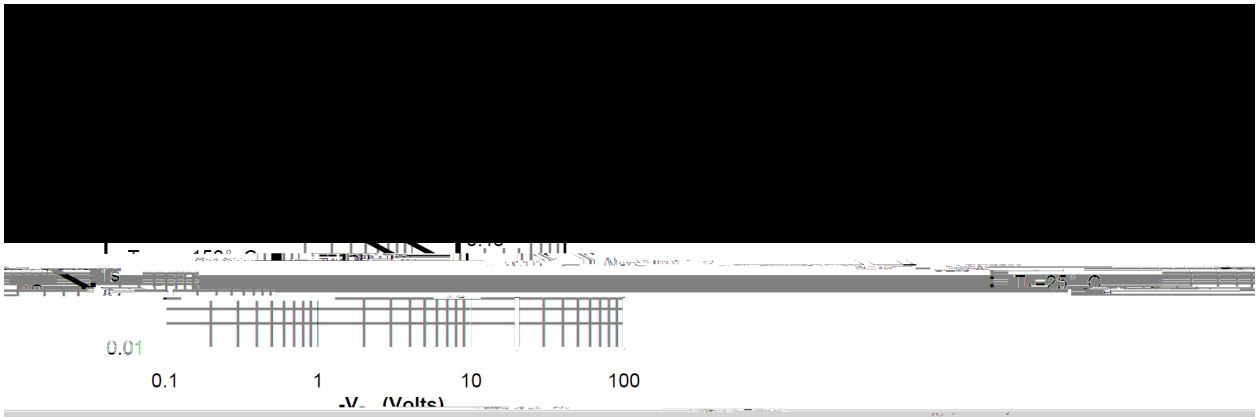
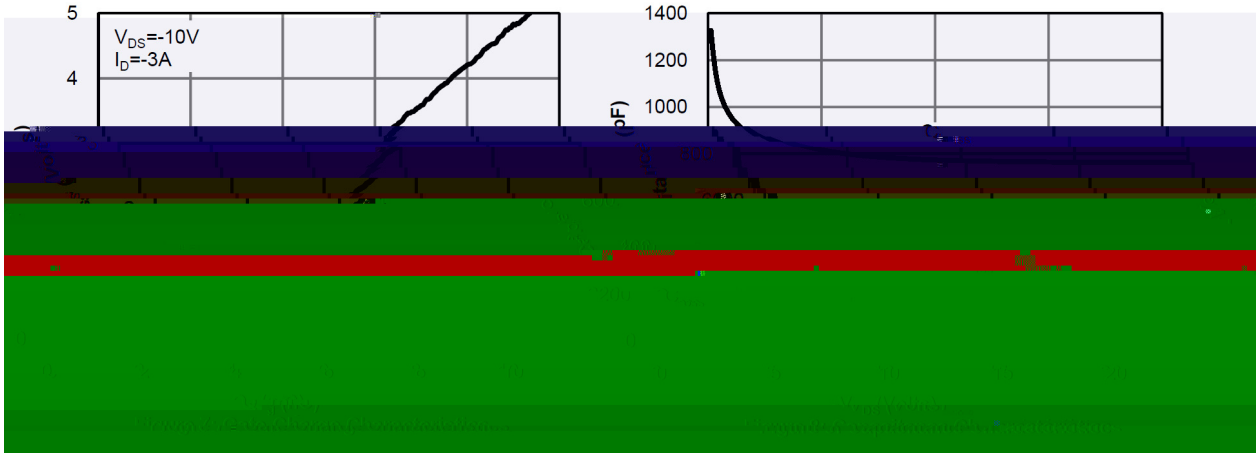
**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20	-23		V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-0.4		-1.0	V
Static Drain–Source On–Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V I <sub>D</sub> =-2A		56	60	m
		V <sub>GS</sub> =-2.5V I <sub>D</sub> =-2A		70	76	m
		V <sub>GS</sub> =-1.8V I <sub>D</sub> =-2A		93	110	m
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V V <sub>GS</sub> =0V			-1.0	μA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V V <sub>DS</sub> =0V			±100	nA
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V I <sub>S</sub> =-1A T <sub>J</sub> =25			-1.2	V
Gate resistance	R <sub>g</sub>	f=1MHz		7.2		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V V <sub>GS</sub> =0V f=1.0MHz		760		pF
Output Capacitance	C <sub>oss</sub>			170		
Reverse Transfer Capacitance	C <sub>rss</sub>			230		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V V <sub>GS</sub> =-4.5V I <sub>D</sub> =-3A		8.7		nC
Gate-to-Source Charge	Q <sub>gs</sub>			1.5		
Gate-to-Drain Charge	Q <sub>gd</sub>			2.3		
Turn–On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> =-10V V <sub>GS</sub> =-4.5V R <sub>L</sub> =3.3 R <sub>GEN</sub> =6		7.3		ns
Turn–On Rise Time	t <sub>r</sub>			25		
Turn–Off Delay Time	t <sub>d(off)</sub>			54		
Turn–Off Fall Time	t <sub>f</sub>			55		

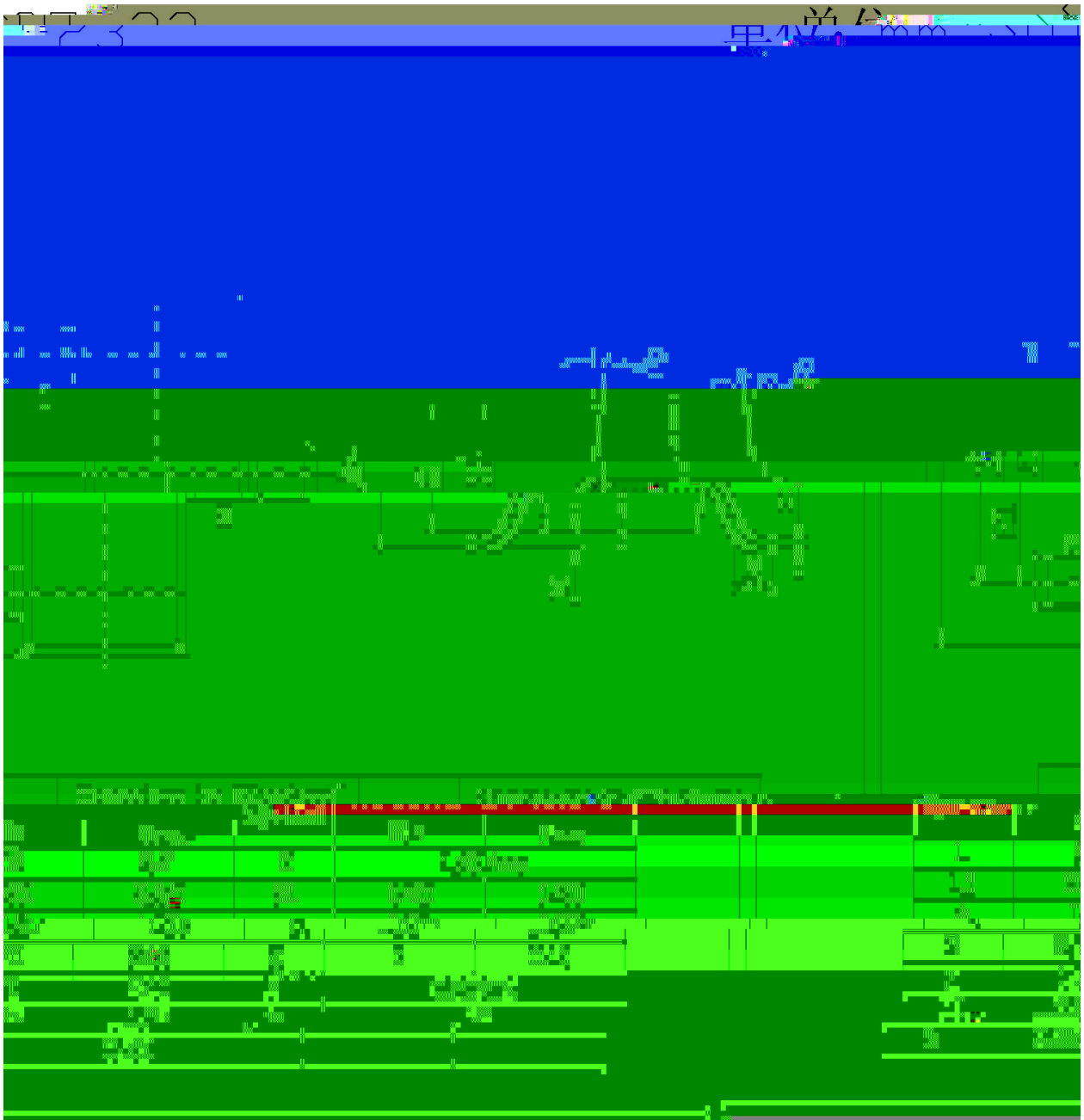
/ Electrical Characteristic Curve

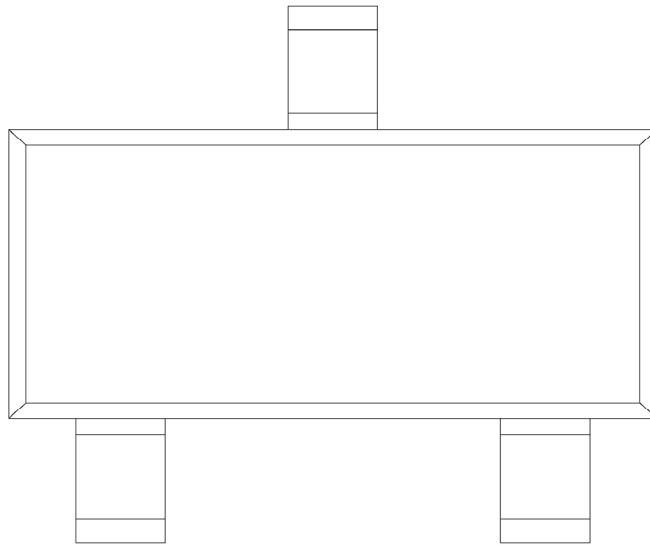


/ Electrical Characteristic Curve



/ Package Dimensions





( ) / Temperature Profile for IR Reflow Soldering (Pb-Free)


- |   |        |     |            |        |  |
|---|--------|-----|------------|--------|--|
|   |        |     |            |        |  |
| 1 | 150    | 180 | 60         | 90sec; | Note:<br>1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245..5 |     | 5..0.5sec; |        | 2.Peak Temp.:245..5 , Duration:5..0.5sec.      |
| 3 |        | 2   | 10         | /sec.  | 3. Cooling Speed: 2~10 /sec.                   |

/ Resistance to Soldering Heat Test Conditions

260..5                      10..1 sec.                      Temp.:260..5                      Time:10..1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension	(unit mm <sup>3</sup> )
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